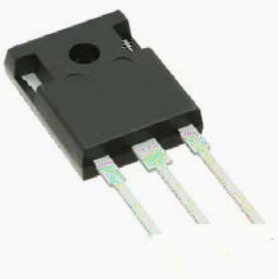
DGW25N120CTL



IGBT Discrete

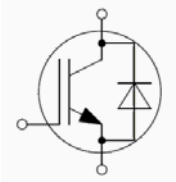
Applications

-
-
-

Features

-
-
-
-
-

Circuit



■Maximum Ratings

Parameter	Symbol	Value	Unit

3ˢ ö PŰ ˅ R 0

jmax T_C= 25 Á C T_C= 100 Á C			

■Electrical Characteristics of the IGBT

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						

■Electrical Characteristics of the Diode

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						

■Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
[redacted]						
[redacted]						
[redacted]						

[redacted]

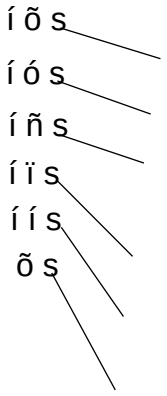
[redacted]

[redacted]

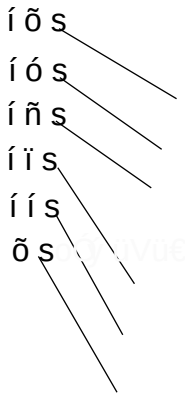
■Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T_j= 25 ;						
Dynamic , at Tj= 125 ;						

Tv$_j$=25



Tv$_j$=150



—— Eon
------ Eoff

V_{CC}=600V
I_C=25A
V_{GE}=±15V
Tv_j=150

Tv_j ≤ 175

—— T_{vj}=25
------ T_{vj}=150

V_{CC}=600V
R_G=18ohm
V_{GE}=±15V
Tv_j=150

V_{CC}=600V
I_F=25A
V_{GE}=±15V
Tv_j=150

i:	1	2	3	4
ri[K/W]	0.0840	0.1780	0.4100	0.3270
£i[s]	0.0723	0.00813	0.00109	0.000155

v&LUFXLW 'LDJUDP

v3DFNDJH 2XWOLQH ,QIRUPDWLRQ

&$6(72